N-Channel Silicon MOSFET



CPH3414

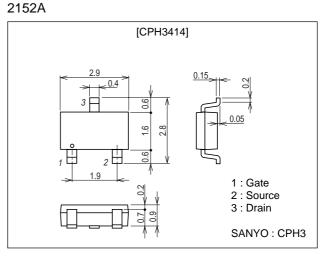
Ultrahigh-Speed Switching Applications

Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 4V drive.

Package Dimensions

unit : mm



Specifications Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		30	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	۱ _D		2.2	А
Drain Current (Pulse)	IDP	PW≤10µs, duty cycle≤1%	8.8	А
Allowable Power Dissipation	PD	Mounted on a ceramic board (900mm ² X0.8mm)	1.0	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0	30			V
Zero-Gate Voltage Drain Current	IDSS	VDS=30V, VGS=0			1	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0			±10	μΑ
Cutoff Voltage	V _{GS} (off)	V _{DS} =10V, I _D =1mA	1.2		2.6	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =1A	1.4	2.0		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	ID=1A, VGS=10V		115	150	mΩ
	R _{DS} (on)2	I _D =0.5A, V _{GS} =4V		190	270	mΩ

Marking : KP

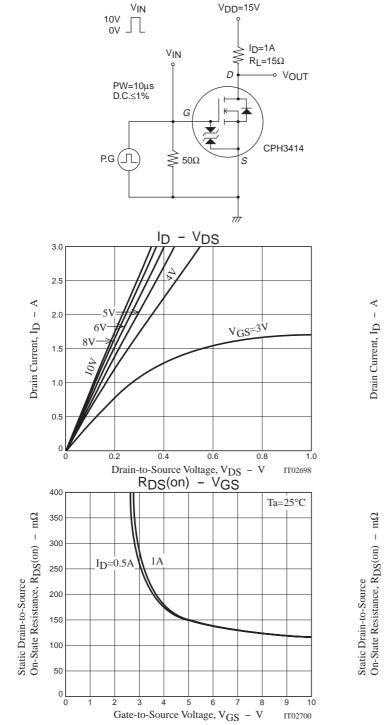
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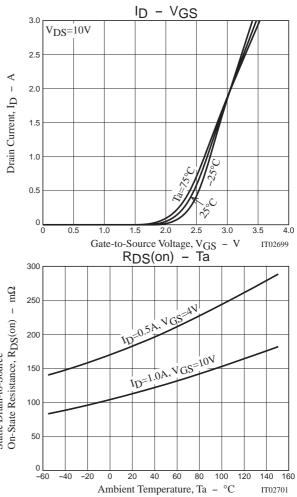
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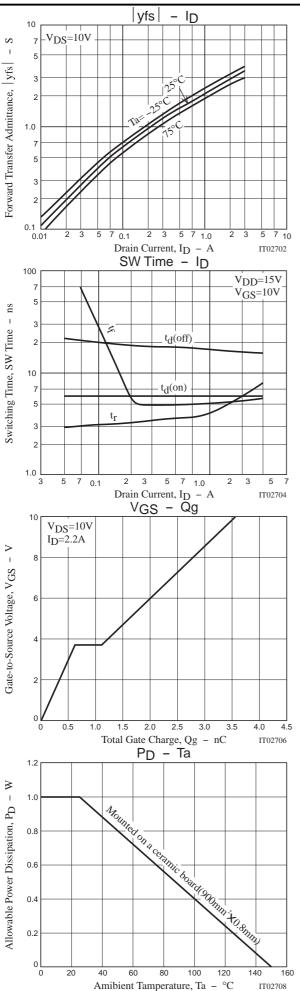
Parameter	Symbol	Conditions		Ratings		
	Symbol		min	typ	max	Unit
Input Capacitance	Ciss	V _{DS} =10V, f=1MHz		120		pF
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		30		pF
Reverse Transfer Capacitance	Crss	VDS=10V, f=1MHz		15		pF
Turn-ON Delay Time	t _d (on)	See specified Test Circuit		6		ns
Rise Time	tr	See specified Test Circuit		4		ns
Turn-OFF Delay Time	td(off)	See specified Test Circuit		17		ns
Fall Time	tf	See specified Test Circuit		5		ns
Total Gate Charge	Qg	V _{DS} =10V, V _{GS} =10V, I _D =2.2A		3.6		nC
Gate-to-Source Charge	Qgs	V _{DS} =10V, V _{GS} =10V, I _D =2.2A		0.6		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =10V, V _{GS} =10V, I _D =2.2A		0.5		nC
Diode Forward Voltage	V _{SD}	IS=2.2A, VGS=0		0.9	1.2	V

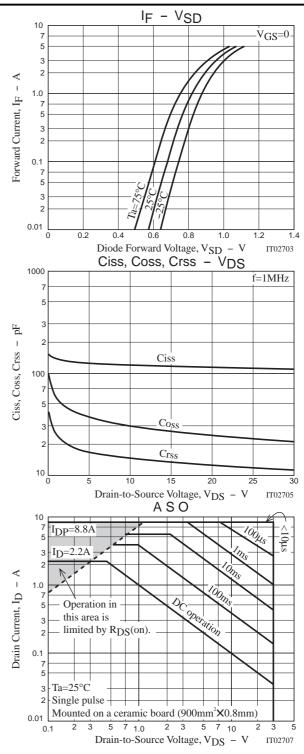
Switching Time Test Circuit





No.6862-2/4





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